

L Number	Hits	Search Text	DB	Time stamp
78	1	("6602620").PN.	USPAT	2003/11/10 11:02
79	1	6602620.pn. and non-magnetic with coercivity and magnetic with coercivity	USPAT	2003/11/10 11:04
80	0	non-magnetic with coercive	USPAT	2003/11/10 11:05
81	385	non-magnetic with coercive	USPAT	2003/11/10 11:05
-	1396	mask with pattern with magnetic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 13:57
-	325	(mask with pattern with magnetic same layer record\$3 and pholithography and plasma and etch\$3 and lithography) and @ad<20000419	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 10:00
-	102	((mask with pattern with magnetic same layer record\$3 and pholithography and plasma and etch\$3 and lithography) and @ad<20000419) and (disc disk)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 14:42
-	107	((mask with pattern with magnetic same layer record\$3 and pholithography and plasma and etch\$3 and lithography) and @ad<20000419) and (disc disk)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 14:43
-	0	mask with pattern with magnetic same layer with record\$3 and pholithography and plasma and etch\$3 and lithography	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 14:45
-	0	mask with pattern with magnetic same layer and pholithography and plasma and etch\$3 and lithography	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 14:44
-	0	mask with pattern with magnetic same layer and pholithography	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 14:44
-	0	mask with pattern with magnetic and pholithography and plasma and etch\$3 and lithography	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 14:45
-	0	mask with pattern with magnetic and pholithography and plasma and etch\$3 and lithography	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 14:46
-	1117	mask with pattern with magnetic and (pholithography and plasma etch\$3 lithography)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 14:47
-	62	mask with pattern with magnetic and (pholithography same plasma pholithography same etch\$3 lithography same plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 14:49
-	18	(mask with pattern with magnetic and (pholithography same plasma pholithography same etch\$3 lithography same plasma)) and @ad<20000419	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 14:50

-	10	((mask with pattern with magnetic and (pholithography same plasma pholithography same etch\$3 lithography same plasma)) and @ad<20000419) and (disc disk)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 14:55
-	10	((mask with pattern with magnetic and (pholithography same plasma pholithography same etch\$3 lithography same plasma)) and @ad<20000419) and (disc disk)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 14:56
-	9	(mask with pattern with magnetic same layer and (pholithography same plasma plasma same etch\$3 and lithography same etch\$3)) and @ad<20000419	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 10:01
-	75	(mask with pattern with magnetic same layer and (pholithography same plasma plasma same etch\$3 lithography same etch\$3)) and @ad<20000419	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:18
-	0	6602620.pn. and block with mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 12:35
-	2	(mask with pattern with magnetic same layer and stamp\$3 and (plasma same etch\$3)) and @ad<20000419	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:20
-	158	(mask with pattern and stamp\$3 and (plasma same etch\$3)) and @ad<20000419	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:21
-	36	(mask with pattern same stamp\$3 and (plasma same etch\$3)) and @ad<20000419	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 15:47
-	0	(mask with pattern same stamp\$3 and (plasma same etch\$3)) and @ad<20000419 and magnet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 16:00
-	0	(mask with pattern same stamp\$3 and (plasma same etch\$3)) and @ad<20000419 and magnet\$%3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 16:00
-	15	(mask with pattern same stamp\$3 and (plasma same etch\$3)) and @ad<20000419 and magnet\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 16:29
-	307	(mask with pattern same (compress\$3 press\$3 stamp\$3) and (plasma same etch\$3)) and @ad<20000419 and magnet\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 16:32
-	7	(mask with pattern same (compress\$3) and (plasma same etch\$3)) and @ad<20000419 and magnet\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 16:32
-	15	(mask with pattern same stamp\$3 and (plasma same etch\$3)) and @ad<20000419 and magnet\$%3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 10:19

-	7	(mask with pattern same compress\$3 and (plasma same etch\$3)) and @ad<20000419 and magnet\$\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 10:20
-	78	mask with pattern same compress\$3 and @ad<20000419 and magnet\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/10 09:22
-	0	428/694.ccls. and mask same pattern	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/10 09:23
-	0	428/694.ccls. and mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/10 09:23
-	0	428/694.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/10 09:24
-	17	428/694r.ccls. and mask same pattern	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/10 10:10
-	42	compress with mask same pattern	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/10 10:55